

Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638 Phone: (562) 404-7855 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

DESIGNER'S DATA SHEET

Part Number / Ordering Information 1/ SDR4 — L Screening^{2/} = None TX = TX Level TXV = TXV Level S = S Level **Package** = Axial SMS = Surface Mount Square Tab Voltage G = 400 VJ = 600 VK = 800 VM = 1000 VN = 1200 V

SDR4G - SDR4N and SDR4GSMS - SDR4NSMS

3 AMP 400 – 1200 Volts 50-80 nsec ULTRA FAST RECTIFIER

Features:

- Ultra Fast Recovery: 50-80 nsec Max. @ 25℃ 85-125 nsec Max. @ 100℃
- Single Chip Construction
- PIV to 1200 Volts
- Low Reverse Leakage Current
- Hermetically Sealed
- For High Efficiency Applications
- Available in Axial Leaded & Surface Mount versions
- Metallurgically Bonded
- TX, TXV, and S-Level Screening Available^{2/}

Maximum Ratings			Symbol	Value	Units
Peak Repetitive Reverse and DC Blocking Voltage SDR4J SDR4K SDR4M SDR4N		$egin{array}{c} egin{array}{c} egin{array}$	400 600 800 1000 1200 Volts		
Average Rectified Forward Current (Resistive Load, 60 Hz Sine Wave, T _A = 25°C)			Io	3	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on Io, Allow Junction to Reach Equilibrium Between Pulses, T _A = 25°C)			I_{FSM}	75	Amps
Operating & Storage Temperature		Top & Tstg	-65 to +175	°C	
Maximum Thermal Resistance		n to Lead, L = 3/8 " Junction to End Tab	$\mathbf{R}_{ heta \mathrm{JL}} \ \mathbf{R}_{ heta \mathrm{JE}}$	20 14	°C/W

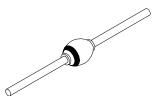
Notes:

 $\underline{1}/$ For Ordering Information, Price, Operating Curves, and Availability – Contact Factory.

2/ Screening Based on MIL-PRF-19500. Screening Flows Available on Request.

Axial Leaded

SMS (Square)







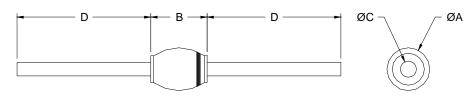
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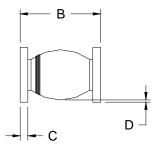
Electrical Characteristics	Part Type	Symbol	Max	Units
Instantaneous Forward Voltage Drop (I _F = 3 Adc, T _A = 25°C, 300 µs pulse)	SDR2G – J SDR2K – N	$ m V_F$	1.9 2.1	Vdc
Instantaneous Forward Voltage Drop (I _F = 3 Adc, T _A = -55°C, 300 μs pulse)	SDR2G – J SDR2K – N	$\mathbf{V_F}$	2.1 2.3	Vdc
Reverse Leakage Current (Rated V_R , $T_A = 25^{\circ}C$, 300 µs pulse minimum)		I_R	5	μА
Reverse Leakage Current (Rated V_R , $T_A = 100^{\circ}$ C, 300 µs pulse minimum)		I_R	0.5	μА
Junction Capacitance (V _R = 10 Vdc, T _A = 25°C, f = 1MHz)		$\mathbf{C}_{\mathbf{J}}$	40	pF
Reverse Recovery Time $(I_F=500 \text{ mA}, \ I_R=1 \text{A}, \ I_{RR}=0.25 \text{A}, \ T_A=25 ^{\circ}\text{C})$	SDR2G – J SRS1K SRS1M SRS1N	t_{rr}	50 60 70 80	nsec

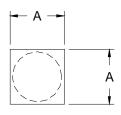




DIMENSIONS					
DIM	MIN	MAX			
A	.120"	.180"			
В	.130"	.230"			
C	.047"	.053"			
D	1.00"				

Case Outline: Surface Mount (SMS)





DIMENSIONS			
DIM	MIN	MAX	
A	0.172"	0.180"	
В	0.180"	0.280"	
C	0.022"	0.028"	
D	0.002"	_	

Dimensions prior to solder dipping